Diode Module

STARPOWER

SEMICONDUCTOR

FD200HFH60C1S

Molding Type Module

600V/200A 2 in one-package

General Description

STARPOWER Diode Power Module provides low forward voltage as well as low reverse recovery loss. They are designed for the applications such as SMPS.

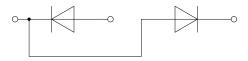
Features

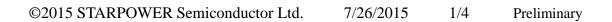
- Fast soft diode
- Low forward voltage drop
- Small temperature coefficient
- Low reverse recovery losses
- High ruggedness
- Low inductance
- Isolated copper baseplate using DBC technology

Typical Applications

- SMPS
- PFC
- Electric welders
- DC choppers

Equivalent Circuit Schematic





FRED



Symbol	Description	Value	Unit	
V _{RRM}	Repetitive Peak Reverse Voltage	600	V	
V _{RSM}	Non-repetitive Peak Reverse Voltage	600	V	
I _{FAV}	Average Forward Current T _C =100 °C,Diode	100	А	
	T _C =100 °C,Module	200		
I _{FSM}	Surge Forward Current $V_R=0V_{,t_p}=10m_{,t_j}=25^{\circ}C$	1600	А	
	$V_{R}=0V, t_{p}=8.3 \text{ ms}, T_{j}=25^{\circ}\text{C}$	1760	A	
I ² t	I^2 t-value $V_R=0V_{,t_p}=10ms, T_j=25^{\circ}C$	12800	A^2s	
	$V_{R}=0V_{t_{p}}=8.3ms_{t_{j}}=25^{\circ}C$	12907		
P _D	Maximum Power Dissipation @ T _j =150°C	579	W	
T _j	Junction Temperature	-40 to +150	°C	
T _{STG}	Storage Temperature Range	-40 to +125	°C	

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Electrical Characteristics of Diode T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
$V_{\rm F}$	Diode Forward	I _F =100A	T _j =25°C		1.35	1.55	v
	Voltage		T _j =125°C		1.30	1.50	
I _R	Diode Reverse	V _R =V _{RRM}	T _i =25°C			0.5	mA
	Current		T _j =125°C			1.0	
t _{rr}	Reverse Recovery	I _F =100A V _R =300V di/dt=-200A/µs	T _j =25°C		78		ns
	Time		T _j =125°C		145		
I _{RM}	Peak Reverse		T _j =25°C		7.8		A
	Recovery Current		T _j =125°C		15.2		
Qr	Reverse Recovery		T _j =25°C		402		nC
	Charge		T _j =125°C		1150		

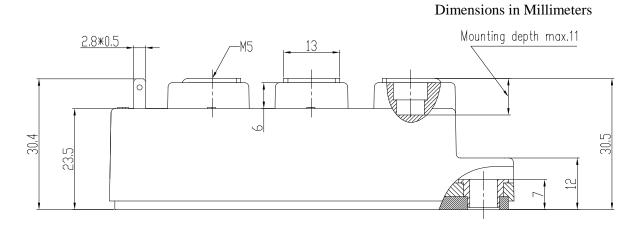
Thermal Characteristics

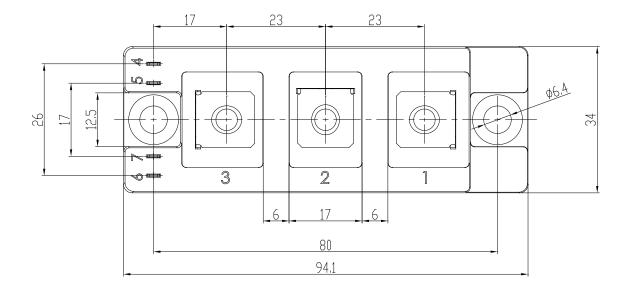
Symbol	Parameter	Min.	Тур.	Max.	Unit
L _{CE}	Stray Inductance			30	nH
R _{CC'+EE'}	Module Lead Resistance, Terminal to Chip		0.75		mΩ
R _{thJC}	Junction-to-Case (per Diode)			0.315	K/W
R _{thCH}	Case-to-Heatsink (per Module)		0.050		K/W
М	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		150		g

Equivalent Circuit Schematic



Package Dimensions





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